Product data sheet

1. General description

Dual ultrafast power diode in a SOT226A (I2PAK) low-profile plastic package.

2. Features and benefits

- · High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state loss

3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	l l	Min	Тур	Max	Unit
V _R	reverse voltage	DC	-	-	-	200	V
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	-	-	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	-	-	160	Α
Static chara	cteristics						
V _F	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 4</u>	-	-	0.78	0.85	V
		I _F = 15 A; T _j = 25 °C; <u>Fig. 4</u>	-	-	0.95	1.05	V
		I _F = 30 A; T _j = 25 °C; <u>Fig. 4</u>	-	-	1	1.2	V
Dynamic cha	aracteristics						
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/ μ s; T_j = 25 °C; ramp recovery; Fig. 5	-	-	20	28	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1 A2
2	K	cathode		
3	A2	anode 2	0	K sym125
mb	К	mounting base; connected to cathode	1 2 3	
			I2PAK (SOT226A)	

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BYV42G-200	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226A			

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7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IFC 60134)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V_R	reverse voltage	DC	-	200	V
I _{O(AV)}	average output current	δ = 0.5; T _{mb} ≤ 104 °C; SQW; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	30	Α
I _{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 μ s; T_{mb} ≤ 104 °C; per diode	-	30	Α
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	150	Α
	forward current	t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN; per diode	-	160	Α
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s	-	0.2	Α
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	-	0.2	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ; all pins	-	8	kV

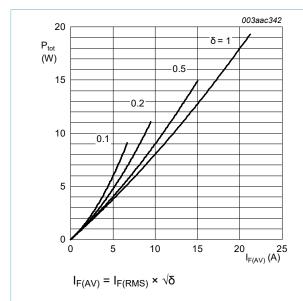


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

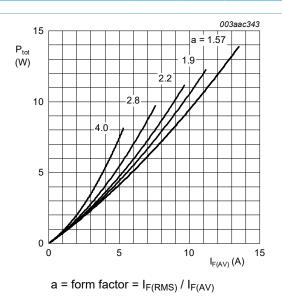


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Dual ultrafast power diode

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.4	K/W
	mounting base	with heatsink compound; per diode; Fig. 3	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

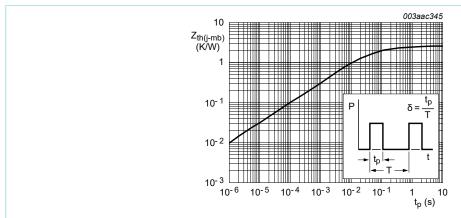


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

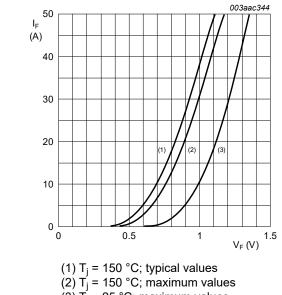
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.78	0.85	V
		I _F = 15 A; T _j = 25 °C; <u>Fig. 4</u>	-	0.95	1.05	V
		I _F = 30 A; T _j = 25 °C; <u>Fig. 4</u>	-	1	1.2	V
I _R	reverse current	V _R = 200 V; T _j = 100 °C	-	0.5	1	mA
		V _R = 200 V; T _j = 25 °C	-	10	100	μA
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5	-	20	28	ns
		I_F = 0.5 A; I_R = 1 A; T_j = 25 °C; step recovery; measured at reverse current = 0.25 A; Fig. 6	-	13	22	ns
Q _r	recovered charge	I_F = 2 A; V_R = 30 V; dI_F/dt = 20 A/ μ s; T_j = 25 °C	-	6	15	nC
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}; T_j = 25 °C;$ Fig. 7	-	-	1	V



(3) $T_i = 25$ °C; maximum values



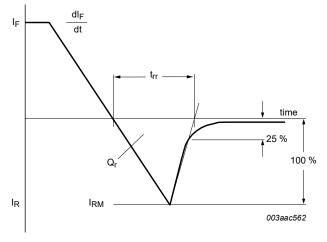
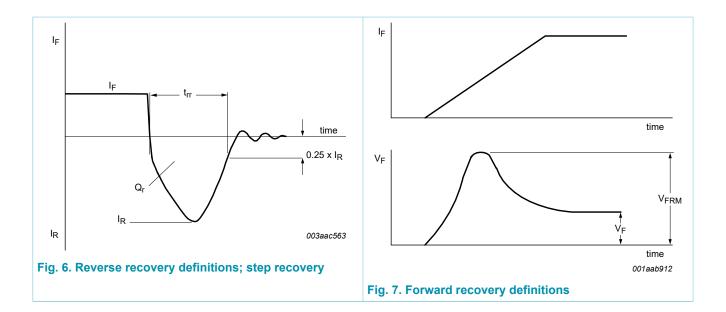


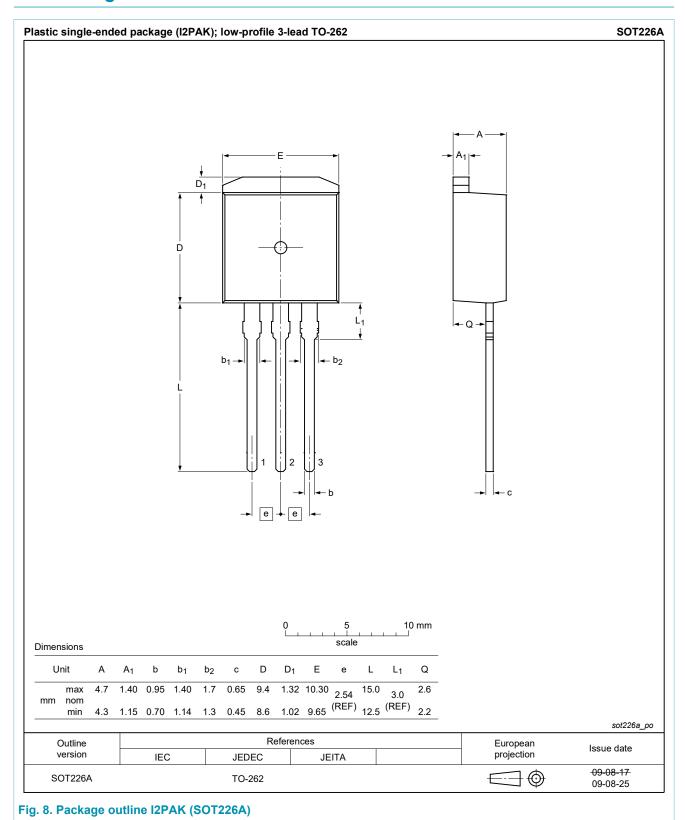
Fig. 5. Reverse recovery definitions; ramp recovery

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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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